# RICOH

# **R5435x SERIES**

# Li-ION/POLYMER 2/3-CELL PROTECTOR Second protection IC

NO.EA-282-120409

# OUTLINES

R5435x Series are CMOS-based high voltage tolerant over-charge protection ICs for Li-ion/Li-polymer secondary battery. The R5435x can detect overcharge of 2-cell to 3-cell Li-ion/Li-polymer batteries. The R5435x is consists of 3 voltage detectors, a voltage reference unit, an oscillator, a counter, a delay circuit, a logic circuit.

When the over-charge is detected, after the IC internally fixed delay time, the output of C<sub>OUT</sub> becomes "H". After detecting over-charge, when the cell voltage becomes lower than the over-charge released voltage, the over-charge state is released.

If all the cells voltages become equal or less than the shutdown detector threshold, all the circuits are halted and shut down, as a result, the consumption current of IC itself (Shutdown current) is extremely reduced.

By connect short 2 cells other than monitored cell, over-charge and released delay time can be shortened. The output type is CMOS.

# FEATURES

Manufactured with High Voltage Tolerant Process Absolute Maximum Rating 30V			
Low supply current	Cell voltage 3.9V, for 3	-cell	Тур. 3.0µА
High accuracy detector threshold	Over-charge detector	(Ta=25°C)	±20mV
		(Ta=0 to 60°C)	±25mV
<ul> <li>Variety of detector threshold</li> </ul>			
Over-charge detector threshold	4.1V-4.55V step of 0.00	5V (Vdet1n) (n=1, 2, 3)	
Over-charge released voltage	VDET1n-0V to VDET1n-0.4	V step of 0.05V (VREL1N) (	n=1, 2, 3)
	MIN.3.95V		
Setting of Output delay time	Over-charge detector Ou	tput Delay options 2, 4, 6s(E	Built-in delay)
Shutdown Function	When all the cell volta	ges become equal or less	s than shutdown
detector threshold, the IC will be into shutdown m	node and the consumption	current of IC itself becomes	extremely small.
Even if one of the cells becomes equal or more th	an shutdown released volta	ge, the shutdown mode is re	eleased.
Shutdown detector threshold	Typ. 3.5V±0.4V		
Shutdown Release Hysteresis	none		
Shutdown current	Max. 0.1µA		
2/3 cell protection enabler	By external wiring, 2 o	r 3-cell protection can be	selected.
Over-charge released condition	Released by voltage ty	vpe	
• Cout output	Cout: 4.7V regulator po	ower supply CMOS output	t. Active "H"
Delay Time Shortening Function	As a result of specified	d setting, the delay times	are shortened,
over-charge detector time is shortened from 2	2sec to 1/50, 4sec and 6	sec to 1/80.	
ex. $V_{C2}=V_{C3}=V_{SS}$ , the delay time for cell 1 is sho	ortened. Vc1=Vc2, Vc3=Vss	, the delay time for cell 2	is shortened.
$V_{C1}=V_{C2}=V_{C3}$ , the delay time for cell 3 is short	ened.		
Small package	TSOT-23-6, DFN(PLP)	1616-6B	

# **BLOCK DIAGRAM**



# **SELECTION GUIDE**

In the R5435Xxxxx Series, input threshold of over-charge and output delay time can be designated according to the application.

Part Number is designated as follows:

(ex.)

C R5435N 301 ↑ ↑ a b	$\uparrow\uparrow$
Code	Contents
а	Package Type N: TSOT-23-6, K: PLP1616-6B
b	Serial Number for the R5435 Series designating input threshold for over-charge detector
С	Designation of Output delay option
d	Designation of version symbols.

### Code List

Code	<b>V</b> DET1 <b>n(V)</b> *1	<b>V</b> REL1 <b>n(V)</b> *1	tVdet1(s)	tVdtr1(ms)
R5435x301AA	4.450	4.150	2	16
R5435x302BA	4.350	3.950	4	16
R5435x303AA	4.350	4.050	2	16
R5435x303CA	4.350	4.050	6	6
R5435x304AA	4.400	4.100	2	16
R5435x305AA	4.300	4.000	2	16
R5435x306BA	4.450	3.950	4	16

\*1: n=1, 2, 3

# **PIN CONFIGURATIONS**



### DFN(PLP)1616-6B



# **PIN DESCRIPTION**

### TSOT-23-6

Pin No.	Symbol	Description
1	Vdd	V <sub>DD</sub> Pin
2	Vc1	Positive terminal pin for Cell-1
3	Vc2	Positive terminal pin for Cell-2
4	Vсз	Positive terminal Pin for Cell-3
5	Vss	Vss pin. Ground pin for the IC
6	Соит	Output pin of over-charge detection

### DFN(PLP)1616-6B

Pin No.	Symbol	Description
1	Vc2	Positive terminal pin for Cell-2
2	Vc1	Positive terminal pin for Cell-1
3	Vdd	VDD Pin
4	Соит	Output pin of over-charge detection
5	Vss	Vss pin. Ground pin for the IC
6	Vсз	Positive terminal Pin for Cell-3

\*The tab voltage level of the backside of the package is the substrate level (Vss).

Connect the tab to the Vss pin (Recommended) or leave the tab open.

# ABSOLUTE MAXIMUM RATINGS

	Ta=25°C, Vss=0V				
Symbol	Item	Ratings	Unit		
Vdd	Supply voltage	-0.3 to 30	V		
	Input voltage				
Vc1	Positive input pin voltage for Cell-1 Vc2 -0.3 to Vc2+6.5		V		
Vc2	Positive input pin voltage for Cell-2	Vc3 –0.3 to Vc3+6.5	v		
Vсз	Positive input pin voltage for Cell-3	–0.3 to 6.5			
	Output voltage		V		
Vcout	Cour pin voltage	-0.3 to Vон1+0.3	v		
PD	Dower dissipation	460 (TSOT-23-6)	m)//		
PD	Power dissipation	640 (PLP1616-6B)	mW		
Та	Operating temperature range	-40 to 85	°C		
Tstg	Storage temperature range	-55 to 125	°C		

# **ELECTRICAL CHARACTERISTICS**

### • R5435x301AA

•	-357301777	l	Jnless othe	rwise spec	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
)/p	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.430	4 450	4.470	
Vdet1 <b>n</b>	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.425	4.450	4.475	V
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.100	4.150	4.200	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsнт	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Vон1	Cout Pch ON voltage1	Іон=0µА, Vселл=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vселл=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Ізнт	Shutdown Current	VCELLN=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	VCELLN=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested. \*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

### R5435x302BA

		l	Jnless othe	rwise speci	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
Vdet1 <b>n</b>	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4.350	4.370	
VDETI	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.325	4.330	4.375	V
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.900	3.950	4.000	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	3.2	4.0	4.8	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsнт	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Vон1	Cout Pch ON voltage1	Іон=0µА, Vселл=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vселл=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Ιοι=50μΑ, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
ISHT	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	VCELLN=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested.

\*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

# **RICOH**

### • R5435x303AA

•	400800000	ι	Jnless othe	rwise spec	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
Varia	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4 250	4.370	v
Vdet1 <b>n</b>	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.325	4.350	4.375	v
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.000	4.050	4.100	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsнт	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Voh1	Cout Pch ON voltage1	Іон=0µА, Vсецип=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vcelln=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Isнт	Shutdown Current	VCELLN=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested.

\*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

### R5435x303CA

		l	Jnless othe	rwise spec	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-VSS	3.3		15	V
Varia	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4.350	4.370	V
Vdet1 <b>n</b>	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.325	4.350	4.375	V
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.000	4.050	4.100	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	4.8	6.0	7.2	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
VSHT	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	2	6	10	ms
Vон1	Cout Pch ON voltage1	Іон=0µА, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vcelln=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Iol=50µA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Ізнт	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	VCELLN=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested. \*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3  $\,$ 

### R5435x304AA 0

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Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
Vdet1n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.380	4.400	4.420	
VDEIIII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.375	4.400	4.425	V
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.050	4.100	4.150	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	s
$tV_{REL1}$	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
VSHT	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Vон1	Cout Pch ON voltage1	Іон=0µА, Vселл=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vселл=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Iol=50μA, VCELLN=3.9V (n=1,2,3)		0.1	0.5	V
SHT	Shutdown Current	VCELLN=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	VCELLN=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested.

\*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

### R5435x305AA

•		l	Jnless othe	rwise spec	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
Vdet1 <b>n</b>	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.280	4.300	4.320	V
V DE I 1 <b>I I</b>	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.275	4.300	4.325	
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.950	4.000	4.050	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsнт	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Vон1	Cout Pch ON voltage1	Іон=0µА, Vселл=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vселл=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Ιοι=50μΑ, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
ISHT	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested. \*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

### • R5435x306BA

		l	Jnless othe	rwise spec	ified, Ta=	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vdd1	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V <sub>DET1</sub> n	CELLn Over-charge threshold (n=1,2,3)	Detect rising edge of supply voltage (25°C)	4.430	4.450	4.470	- V
		Detect rising edge of supply voltage (0 to 60°C) <sup>*Note1</sup>	4.425	4.450	4.475	
V <sub>REL1</sub> n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.900	3.950	4.000	V
tVdet1	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	3.2	4.0	4.8	s
tV <sub>REL1</sub>	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsнт	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tVdtr1	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
Voh1	Cout Pch ON voltage1	Іон=0µА, Vсецип=4.7V (n=1,2,3)	4.0	4.7	5.4	V
Vон2	Cout Pch ON voltage2	Іон=-50µА, Vселл=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Cout Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
ISHT	Shutdown Current	VCELLN=3.1V (n=1,2,3)			0.1	μA
lss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μA

\*Note1: This specification is guaranteed by design, not mass production tested.

\*Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

### **RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)**

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

### OPERATION

### VDET1n / Over-Charge Detectors (n=1, 2, 3)

While the cells are charged, the voltage between  $V_{C1}$  pin and  $V_{C2}$  pin (voltage of the Cell-1), the voltage between  $V_{C2}$  pin and  $V_{C3}$  pin (voltage of the Cell-2), and the voltage between  $V_{C3}$  pin and  $V_{ss}$  pin (voltage of the Cell-3) are supervised. If at least one of the cells' voltage becomes equal or more than the over-charge detector threshold, the over-charge is detected, and an external charge control Nch MOSFET turns on with  $C_{OUT}$  pin being at "H" level and by cutting a fuse on the charger path, and charge stops.

To reset the over-charge and make the  $C_{OUT}$  pin level to "L" again after detecting over-charge, in such conditions that a time when all the cells' voltages are down to a level lower than over-charge released voltage.

Internal fixed output delay times for over-charge detection, over-charge detector timer reset, release from over-charge exist. Even if one of voltage of the cells keeps its level more than the over-charge detector threshold, and output delay time passes, over-charge voltage is detected. If all the cell voltages become lower than the over-charge detector threshold within the output delay time of over-chare detector by noise or other reasons, the time period is less than over-charge detector timer reset output delay time, the over-charge delay time is accumulated and maintained, and the accumulated delay time reaches the output delay time of over-charge is detected. After detecting over-charge, even if all the cell voltages become equal or less than the released voltage from over-charge, if at least one of the cells voltage becomes higher than the released voltage from over-charge within the output delay time of the release from over-charge, then over-charge is not released.

The output type of the Cout pin is CMOS output between Vss and the built-in regulator, and "H" level of Cout pin is the output voltage of the built-in regulator. (Typ. 4.7V)

### Shutdown Function

The voltage between V<sub>C1</sub> pin and V<sub>C2</sub> pin (the voltage of Cell-1), the voltage between V<sub>C2</sub> pin and V<sub>C3</sub> pin (Cell-2 voltage), and the voltage between V<sub>C3</sub> pin and V<sub>SS</sub> pin (Cell-3 voltage) are supervised. If all the cells voltages become equal or less than the shutdown detector threshold, all the circuits are halted and shut down, as a result, the consumption current of IC itself (Shutdown current) is extremely reduced. (Max.  $0.1\mu$ A)

After detecting shutdown, at least one of the cell voltages becomes equal or more than the shutdown detector threshold, the shutdown state is released.

### • DS (Delay Shortening) Function

By connect short 2 cells other than monitored cell, over-charge and released delay time can be shortened. Table of the cell of delay time shortened and direct wiring positions

Delay time shortened CELL	Direct wiring positions	
CELL1	$V_{\text{C2}}$ pin and $V_{\text{C3}}$ pin, $V_{\text{C3}}$ pin and $V_{\text{SS}}$ pin	
CELL2	$V_{C1}$ pin and $V_{C2}$ pin, $V_{C3}$ pin and $V_{SS}$ pin	
CELL3	$V_{\text{C1}}$ pin and $V_{\text{C2}}$ pin, $V_{\text{C2}}$ pin and $V_{\text{C3}}$ pin	

### • 2-cell/ 3-cell protection alternative

When the IC should be used as a 2-cell protection IC, connect short  $V_{C3}$  pin and  $V_{SS}$  pin.

# **TIMING CHART**

Over-charge operation



# **TYPICAL APPLICATIONS**

### (1) Circuit example (3-cell protection)



\*In terms of the order of connecting cells, the positive terminal of the cell 1 should be the last. Otherwise, COUT may output "H" tentatively, and the fuse may be fused.

### External parts ratings

Symbol	Тур.	Unit	Range
Rvdd	100	Ω	100~1000
R1	1000	Ω	330~1000
R2	1000	Ω	330~1000
R3	1000	Ω	330~1000
CVDD	0.1	uF	0.01~1
C1	0.1	uF	0.01~1
C2	0.1	uF	0.01~1
C3	0.1	uF	0.01~1

## **Technical Notes**

The voltage fluctuation is stabilized with R<sub>VDD</sub> and C<sub>VDD</sub>. If a small R<sub>VDD</sub> is set, in the case of the large transient may happen to the cell voltage, by the flowing current, the IC may be unstable. If a large R<sub>VDD</sub> is set, by the consumption current of the IC itself, the voltage difference between V<sub>DD</sub> pin and V<sub>C1</sub> pin is generated, and unexpected operation may result. Therefore, the appropriate value range of R<sub>VDD</sub> is from 100 $\Omega$  to 1k $\Omega$ . To make a stable operation of the IC, the appropriate value range of C<sub>VDD</sub> is from 0.01µF to 1.0µF.

The voltage fluctuation is stabilized with R1 to R3 and C1 to C3. If a R1 to R3 is too large, by the conduction current at detection, the detector threshold may shift higher. Therefore, the appropriate value range of R1 to R3 is equal or less than  $1k\Omega$ . To make a stable operation of the IC, the appropriate value range of C1 to C3 is  $0.01\mu$ F or more.

The typical application circuit diagrams are just examples. This circuit performance largely depends on the PCB layout and external components. In the actual application, fully evaluation is necessary.

Over-voltage and the over current beyond the absolute maximum rating should not be forced to the protection IC and external components. During the time until the fuse is open after detecting over-charge, a large current may flow through the FET. Select an FET with large enough current capacity in order to endure the large current.

Ricoh cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Ricoh product. If technical notes are not complied with the circuit which is used Ricoh product, Ricoh is not responsible for any damages and any accidents.

To connect the SC protector, connect the SC protector to the cell must be the last.

\*SC protector

Contact: Sony Chemical & Information Device Company Ltd. Zip code 141-0032

1-11-2 Osaki, Shinagawa, Tokyo Gate-city Osaki East Tower 8F Phone 03-5435-3946 http://www.sonycid.jp

# **TEST CIRCUITS**





### Typical Characteristics were obtained with using those above circuits:

- Test Circuit A: Typical characteristics 1), 2)
- Test Circuit B: Typical characteristics 3), 4), 6)
- Test Circuit C: Typical characteristics 5)
- Test Circuit D: Typical characteristics 7)
- Test Circuit E: Typical characteristics 8)
- Test Circuit F: Typical characteristics 9)
- Test Circuit G: Typical characteristics 10), 11)

# **TYPICAL CHRACTERSTICS**

### Part1. vs. Temperature

1) Over-charge voltage Threshold (CELLn) vs. Temperature 2) Over-charge Released Voltage (CELLn) vs.



# 3) Output Delay of Over-charge vs. Temperature R5435N301AA



 Over-charge Released Voltage (CELLn) vs. Temperature R5435N301AA



R5435N302BA







# **RICOH**



# 6) Output Delay of Over-charge Timer Reset vs. Temperature 7) Cout Pch ON Voltage 1 vs. Temperature R5435N301AA R5435N301AA











### 9) Cout Nch ON Voltage vs. Temperature R5435N301AA









### Part2. Delay Time dependence on $V_{DD}$ 1) Output Delay of Over-charge vs. $V_{DD}$

2) Output Delay of Release from Over-charge vs.  $V_{\text{DD}}$ 



# $\begin{array}{c|ccccc} & & & & & & & \\ & & & & & & \\ & & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & &$

R5435N302BA

# RICOH



### Part3. Supply Current dependence on V\_DD (R5435N301AA)

3-cell protector Supply Current vs.  $V_{\text{DD}}$ 





Part4. Over-charge detector, Release voltage from Over-charge dependence on External Resistance value (R5435N301AA)

Over-charge Detector/Released Voltage from Over-charge vs. R1 (CELL1)



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Ricoh Electronics: <u>R5435N303AA-TR-FE</u> R5435N304AA-TR-FE



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